

BAS70-04-05-06 SCHOTTKY DIODE

FEATURES

Power dissipation

$$P_D: \quad 200 \quad \text{mW} \quad (T_{amb}=25^\circ\text{C})$$

Collector current

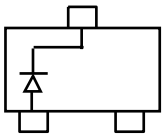
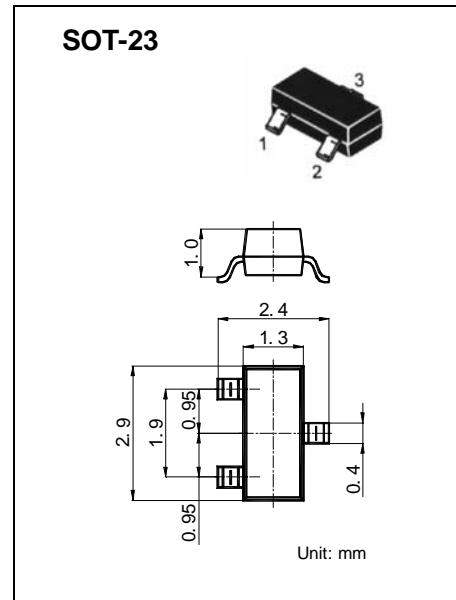
$$I_F: \quad 200 \quad \text{mA}$$

Collector-base voltage

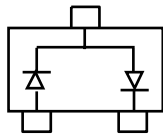
$$V_R: \quad 70 \quad \text{V}$$

Operating and storage junction temperature range

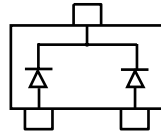
$$T_J, T_{stg}: \quad -55^\circ\text{C} \quad \text{to} \quad +150^\circ\text{C}$$



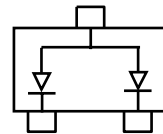
BAS70 Marking: 73



BAS70-04 Marking: 74



BAS70-05 Marking: 75



BAS70-06 Marking: 76

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|---------------------------------|-------------|--|-----|-------------|------|
| Reverse breakdown voltage | $V_{(BR)R}$ | $I_R=10\mu\text{A}$ | 70 | | V |
| Reverse voltage leakage current | I_R | $V_R=50\text{V}$ | | 100 | nA |
| Forward voltage | V_F | $I_F=1\text{mA}$ $I_F=15\text{mA}$ | | 410 1000 | mV |
| Diode capacitance | C_D | $V_R=0\text{V}, f=1\text{MHz}$ | | 2 | pF |
| Reveres recovery time | t_{rr} | $I_F=10\text{mA}$ through $I_R=10\text{mA}$ to $I_R=1\text{mA}$ | | 5 | nS |